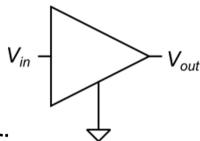
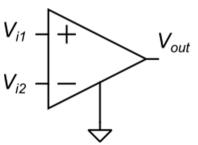
Voltage amplifiers: number of inputs and outputs

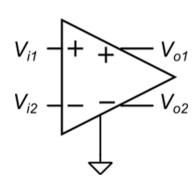


Unipolar:

single input
single output (single-ended, S/E)

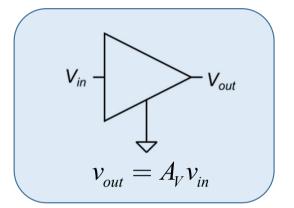


Differential: differential input, single output (single-ended, S/E)



Fully Differential: differential input, differential output

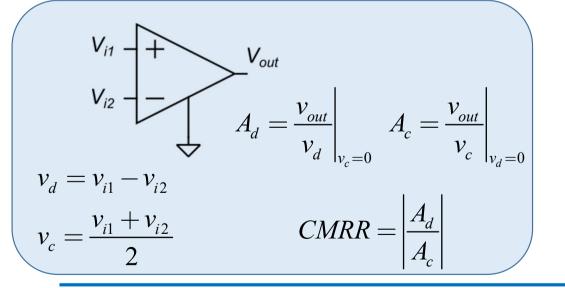
Voltage Amplifiers: gains

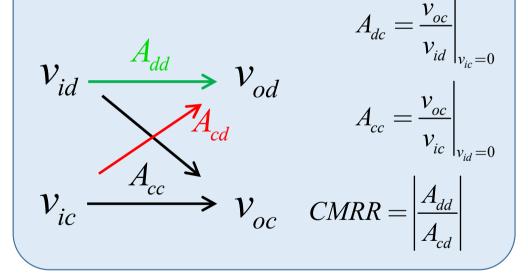


$$v_{id} = v_{i1} - v_{i2} \quad V_{i1} + V_{o1}$$

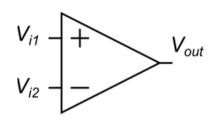
$$v_{ic} = \frac{v_{i1} + v_{i2}}{2} \quad V_{i2} - V_{o2} \quad v_{od} = v_{o1} - v_{o2}$$

$$v_{oc} = \frac{v_{o1} + v_{o2}}{2} \quad A_{cd} = \frac{v_{od}}{v_{ic}} \Big|_{v_{ic} = 0}$$





Differential amplifiers: parameters



$$V_{out} = A_d \left(V_{id} - V_{io} \right)$$

Linear response (with input offset voltage)

Input voltage ranges:

Input differential range (maximum V_{ID} (V_D) to maintain an acceptable input-output linearity

$$-V_{DMAX} \le V_D \le V_{DMAX}$$

Input common-mode range: Interval of VC values where the amplifier behaves as designed

$$V_{CMIN} \le V_C \le V_{CMAX}$$

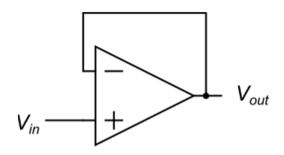
Output voltage range (Output voltage swing)

$$V_{OMIN} \le V_{out} \le V_{OMAX}$$

Outside the output range the amplifier stop working correctly (e.g. the output voltage tends to saturate)

Differential amplifiers: role of the input common mode range

Example: voltage follower (buffer amplifier)



In the ideal case:

$$V_{io}=0, A_d\to\infty$$

We have:

$$V_C = V_{in}$$
 $V_D \cong 0$

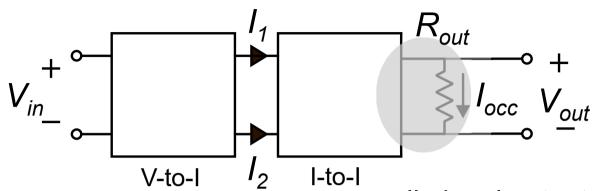
The voltage follower operates correctly only for V_{in} within the CM range

Another condition is clearly that V_{out} is within the output range

Then the conditions for correct operation are:

$$V_{out} = V_{in} \text{ only for } \begin{cases} V_{CMIN} \leq V_{in} \leq V_{CMAX} \\ V_{OMIN} \leq V_{out} \leq V_{OMAX} \end{cases}$$

Single Stage Voltage Amplifiers



small-signal output voltage

$$v_{out} = i_{occ} R_{out}$$

The first component converts the input voltage (single or differential) into a current (single or differential)

The second component is a current processing network, that takes the input currents and applies simple linear operations such as:

- Addition and subtraction
- Addition of constant currents
- Multiplication by a constant gain factor

The processed currents are finally conveyed to an output resistance (R_{out}) and converted back to a voltage (V_{out}). In most cases, Rout is not a physical resistor, but is the output differential resistance of the I-to-I network. For this reason, one of the function of the I-to-I network is increasing the output resistance to increase gain

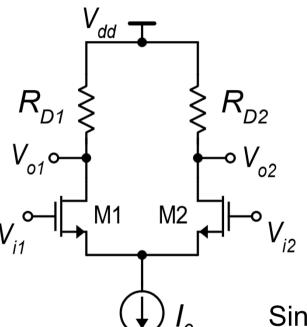
example

$$I_{occ} = k_I (I_1 - I_2) = G_{m1} k_I V_{in}$$
 $v_{out} = G_{m1} k_1 v_{in} R_{out}$
defining: $G_m = k_I G_{m1}$
 $A = G_m R_{out}$

example

$$I_1 - I_2 = G_{m1}V_{in}$$

Differential amplifier with resistive loads



$$V_{ID} = V_{i1} - V_{i2}$$
 $V_{OD} = V_{o1} - V_{o2}$

$$V_{O1} = V_{DD} - R_{D1}I_{D1} \quad V_{O2} = V_{DD} - R_{D2}I_{D2} \quad V_{OD} = R_{D2}I_{D2} - R_{D1}I_{D1}$$
 2

Small signal analysis

$$v_{o1} = -R_{D1}i_{d1}$$
 $v_{o2} = -R_{D2}i_{d2}$ $v_{od} = i_{d2}R_{D2} - i_{d1}R_{D1}$

Differential mode:
$$i_{d1} = \frac{g_m}{2} v_{id}$$
 $i_{d2} = -\frac{g_m}{2} v_{id}$

Single-ended case:

$$v_{out} = v_{o1} = -R_{D1} \frac{g_m}{2} v_{id}$$

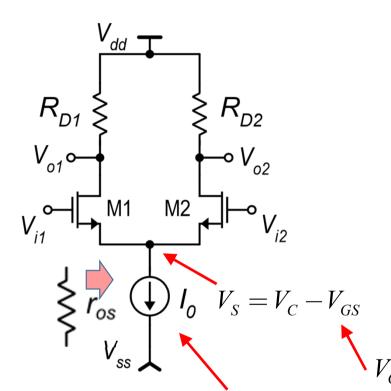
$$A_d = -R_{D1} \frac{g_m}{2}$$

Fully-differential case:

$$v_{out} = v_{od} = -\frac{g_m}{2} (R_{D1} + R_{D2}) v_{id}$$

$$A_{dd} = -g_m \frac{(R_{D1} + R_{D2})}{2}$$

Common mode Analysis



$$V_{id} = 0 \Rightarrow i_{d1} = i_{d2}$$

$$V_{i1} = v_{i2} = v_{c}$$

$$V_{o2}$$

$$i_{0} = i_{d1} + i_{d2} = \frac{v_{s}}{r_{os}}$$

$$v_{s} = v_{i1} - v_{gs1} = v_{c} - v_{gs1}$$

$$V_{GS} \cong constant$$

$$V_{gs1} = \frac{i_{d1}}{g_{m}}$$

$$v_{s} = v_{c} - \frac{i_{d1}}{g_{m}}$$

$$i_{d1} + i_{d2} = 2i_{d1} = i_{0}$$

$$i_{d1} = \frac{i_{0}}{2} = \frac{v_{s}}{2r_{os}}$$

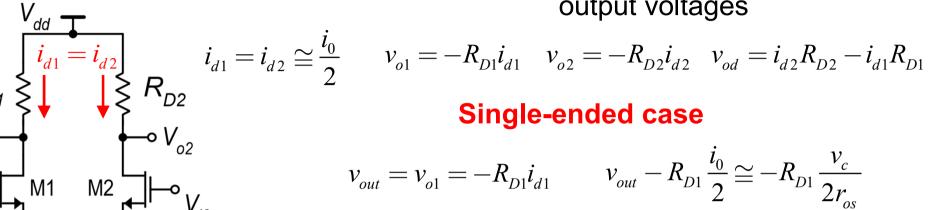
$$v_{s} = v_{c} - \frac{v_{s}}{2r_{os}g_{m}}$$

$$v_{s} = v_{c} \frac{1}{1 + \frac{1}{2g_{m}r_{os}}} \cong v_{c}$$

This, actually, is not an ideal current source. It has a finite output resistance = r_{os} If it is implemented by a simple current mirror, $r_{os} = r_d$ otherwise it can be even higher

The source voltage practically follows the common mode variations. V_S is V_C shifted by V_{GS}

Common mode gain and CMRR



$$i_{d1} = i_{d2} \cong \frac{i_0}{2}$$

$$v_{out} - R_{D1} \frac{i_0}{2} \cong -R_{D1} \frac{v_c}{2r}$$

$$A_c = \frac{v_{out}}{v_c} \bigg|_{v_c = 0} \cong -\frac{R_{D1}}{2r_{os}}$$

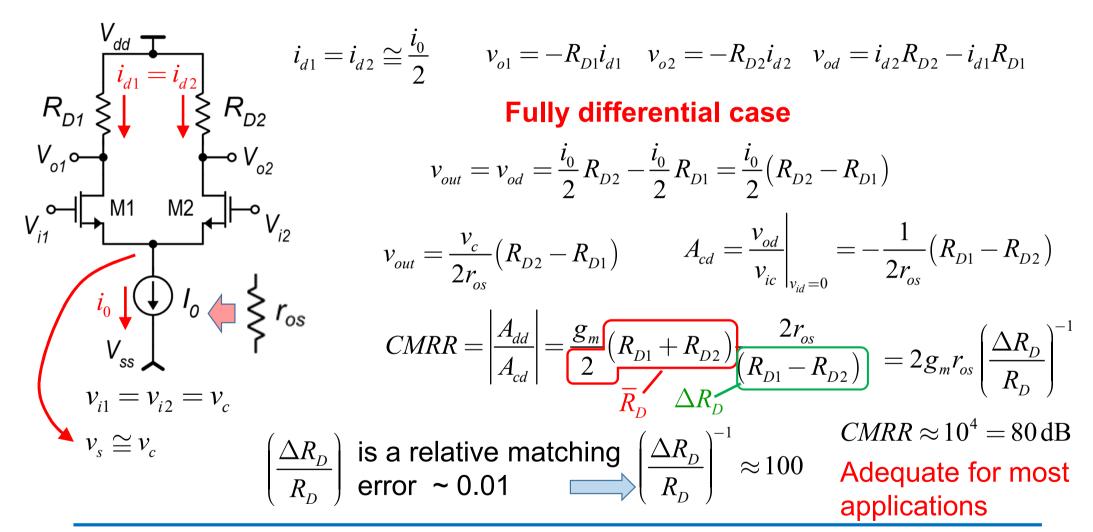
$$A_c = \frac{v_{out}}{v_c} \bigg|_{v_d=0} \cong -\frac{R_{D1}}{2r_{os}}$$
 $CMRR = \frac{A_d}{A_c} = \frac{g_m R_{D1}}{2} \frac{2r_{os}}{R_{D1}}$

$$CMRR = \left| \frac{A_d}{A_c} \right| = g_m r_{os}$$

 $CMRR = \left| \frac{A_d}{A_c} \right| = g_m r_{os}$ Considering that generally I_0 is produced by a simple current mirror, $r_{os} = r_d$, then CMRR~40 dB,

This CMRR is not sufficient for many applications

Common mode gain and CMRR



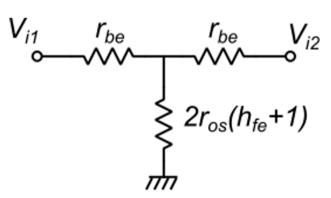
BJT case

 R_{C1} R_{C2} V_{o1} M1 M2 V_{i2} R_{B2} R_{C2} R_{C2}

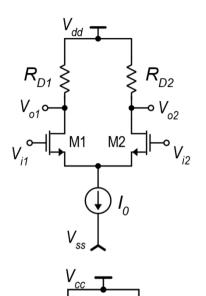
In the case of a BJT differential amplifier, the expressions are exactly the same as for the MOSFET case.

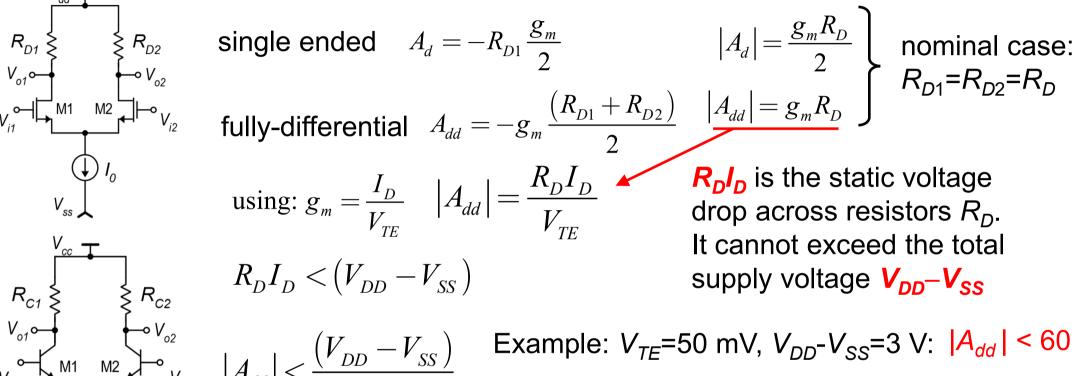
The only important difference is the presence of a base current that is drawn from the voltage sources that provide V_{i1} and V_{i2} . In terms of small signal analysis, this base current is the cause of a finite input resistance that may result in an input attenuation if the signal voltage sources (V_{i1}, V_{i2}) have a significant internal resistance.

Equivalent circuit of the input terminals



Maximum gain for a given supply voltage





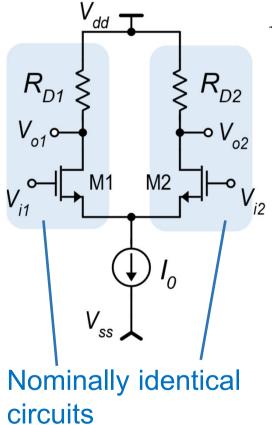
$$|A_d| = \frac{g_m R_D}{2}$$
 nominal case:
$$|A_{dd}| = g_m R_D$$

$$R_{D1} = R_{D2} = R_D$$

$$V_{ss} \downarrow \qquad \text{using: } g_m = \frac{b}{V_{TE}} \quad |A_{dd}| = \frac{b}{V_{TE}} \quad \text{drop across resistors } R_D. \\ \text{It cannot exceed the total supply voltage } V_{DD} - V_{SS} \\ R_{C1} \downarrow V_{O1} - V_{O2} \\ V_{O1} \downarrow V_{O2} \\ V_{O2} \downarrow V_{O2} \\ V_{O2} \downarrow V_{O2} \\ V_{O3} \downarrow V_{O2} \\ V_{O4} \downarrow V_{O2} \\ V_{O2} \downarrow V_{O2} \\ V_{O3} \downarrow V_{O2} \\ V_{O4} \downarrow V_{O2} \\ V_{O2} \downarrow V_{O2} \\ V_{O3} \downarrow V_{O2} \\ V_{O2} \downarrow V_{O3} \\ V_{O2} \downarrow V_{O3} \\ V_{O3} \downarrow V_{O4} \\ V_{O5} \downarrow V_{O2} \\ V_{O4} \downarrow V_{O5} \\ V_{O5} \downarrow V_{O5}$$

to bias the MOSFETS with the smallest V_{TF} .

MOSFET case - fully-differential - Strong inversion



$$v_{io} = V_D \big|_{V_{out}=0}$$

$$V_{out} = V_{o1} - V_{o2}$$

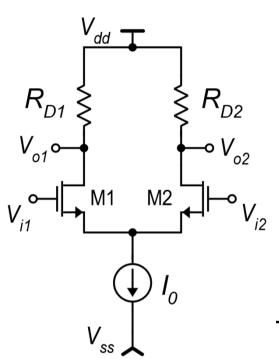
$$V_D = V_{GS1} - V_{GS2} \triangleq \Delta V_{GS}$$

 $\begin{aligned} |V_{io} = V_D|_{V_{out} = 0} & V_D = V_{GS1} - V_{GS2} \triangleq \Delta V_{GS} \\ V_{out} = V_{o1} - V_{o2} & \text{We can consider the difference of V}_{GS} \text{ as the matching error between two nominally identical circuits: M1,R}_{D1} \text{ and M2,R}_{D2} \end{aligned}$ identical circuits: M1,R_{D1} and M2,R_{D2}

$$V_{GS} = V_t + \sqrt{\frac{2I_D}{\beta}} \qquad A = V_t \quad B = \sqrt{\frac{2I_D}{\beta}} = \sqrt{2 \cdot I_D^{\frac{1}{2}} \beta^{-\frac{1}{2}}}$$

$$V_{GS} = A + B \qquad \Delta V_{GS} = \Delta A + \Delta B \qquad \text{form}$$

$$\Delta A = \Delta V_t$$
 $\Delta B = B \cdot \frac{\Delta B}{B} = B \cdot \left[\frac{1}{2} \frac{\Delta I_D}{I_D} - \frac{1}{2} \frac{\Delta \beta}{\beta} \right]$



MOSFET case - fully-differential

$$V_D = \Delta V_{GS} = \Delta A + \Delta B$$

$$V_{D} = \Delta V_{GS} = \Delta A + \Delta B$$

$$V_{GS} = V_{t} + \Delta B$$

$$V_{D} = \Delta V_{t} + \Delta B = B \cdot \left(\frac{1}{2} \frac{\Delta I_{D}}{I_{D}} - \frac{1}{2} \frac{\Delta \beta}{\beta}\right)$$

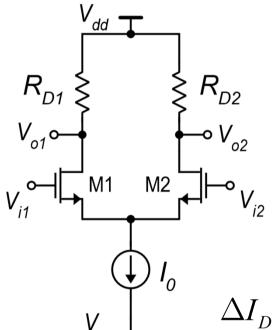
$$V_{i2}$$

$$V_{D} = \Delta V_{GS} = \Delta V_{t} + \sqrt{\frac{2I_{D}}{\beta}} \cdot \left(\frac{1}{2} \frac{\Delta I_{D}}{I_{D}} - \frac{1}{2} \frac{\Delta \beta}{\beta}\right)$$

This is a generic expression of V_D, corresponding to a given value of $\frac{\Delta I_D}{I_D}$

This expression gives V_{io} for the particular $\frac{\Delta I_D}{I_D}$ value that results in V_{out} =0

MOSFET case - fully-differential



$$\begin{cases} R_{D2} & V_{out} = V_{OD} = R_{D2}I_{D2} - R_{D1}I_{D1} \\ V_{o2} & \text{defining: } Z = R_DI_D & \Delta Z = V_{out} \end{cases}$$

Imposing $V_{out}=0$ is the same as imposing $\Delta Z=0$

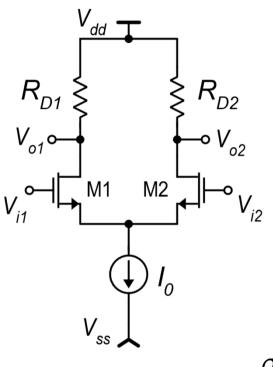
$$\Delta Z = \frac{\Delta Z}{Z} Z = \left(\frac{\Delta R_D}{R_D} + \frac{\Delta I_D}{I_D}\right) R_D I_D = 0$$
 value and cannot be zero

 $R_D I_D$ is the average

$$\frac{\Delta I_D}{I_D} = -\frac{\Delta R_D}{R_D} \longrightarrow V_D = \Delta V_{GS} = \Delta V_t + \sqrt{\frac{2I_D}{\beta}} \cdot \left(\frac{1}{2} \frac{\Delta I_D}{I_D} - \frac{1}{2} \frac{\Delta \beta}{\beta}\right)$$

$$V_{io} = \Delta V_t + \sqrt{\frac{2I_D}{\beta}} \cdot \left(-\frac{1}{2} \frac{\Delta R_D}{R_D} - \frac{1}{2} \frac{\Delta \beta}{\beta} \right) \qquad -\frac{\Delta R_D}{R_D}$$

MOSFET case - fully-differential

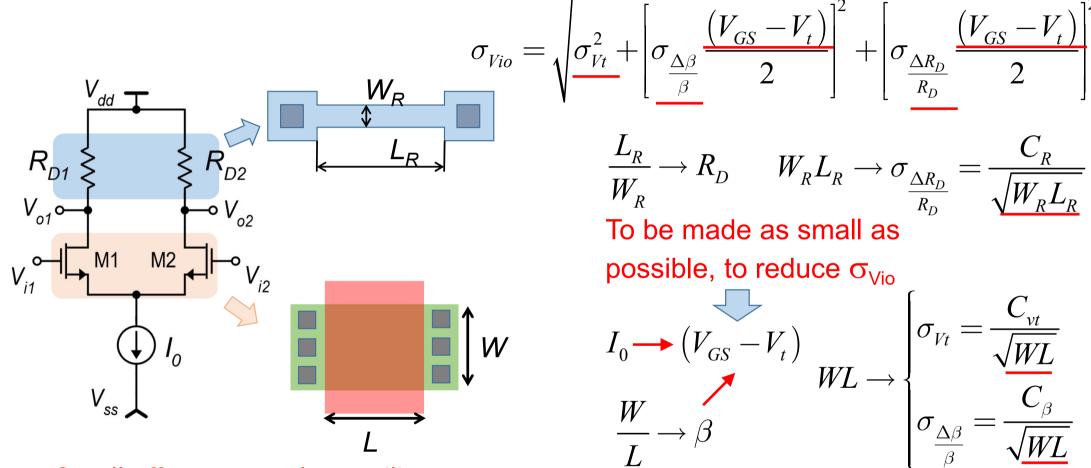


$$\begin{cases} R_{D2} & V_{io} = \Delta V_t + \sqrt{\frac{2I_D}{\beta}} \cdot \left(-\frac{1}{2} \frac{\Delta R_D}{R_D} - \frac{1}{2} \frac{\Delta \beta}{\beta} \right) \end{cases}$$

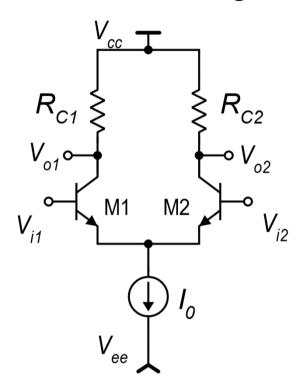
$$V_{io} = \Delta V_t - \frac{\left(V_{GS} - V_t\right)}{2} \left(\frac{\Delta R_D}{R_D} + \frac{\Delta \beta}{\beta}\right)$$

$$\sigma_{Vio} = \sqrt{\sigma_{Vt}^2 + \left[\sigma_{\frac{\Delta\beta}{\beta}} \frac{\left(V_{GS} - V_t\right)}{2}\right]^2 + \left[\sigma_{\frac{\Delta R_D}{R_D}} \frac{\left(V_{GS} - V_t\right)}{2}\right]^2}$$

Role of the design parameters



Small offset means large silicon area

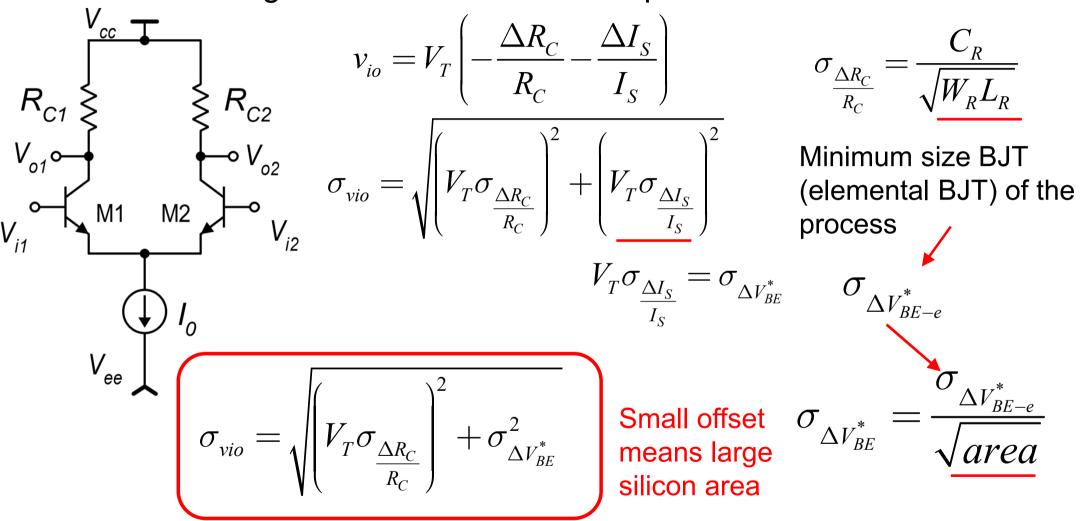


$$v_{io} = V_{id} \big|_{V_{od} = 0}$$
 $V_{od} = V_{o1} - V_{o2} = R_{C2}I_{C2} - R_{C2}I_{C2}$

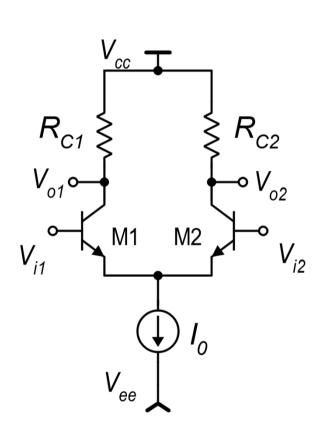
$$V_{id} = V_{i1} - V_{i2} = V_{BE1} - V_{BE2} = \Delta V_{BE}$$

$$V_{od} = 0 \implies \Delta(R_C I_C) = 0 \implies \frac{\Delta I_C}{I_C} = -\frac{\Delta R_C}{R_C}$$

$$v_{io} = V_T \left(-\frac{\Delta R_C}{R_C} - \frac{\Delta I_S}{I_S} \right)$$



Temperature drift of the input offset voltage: BJT case



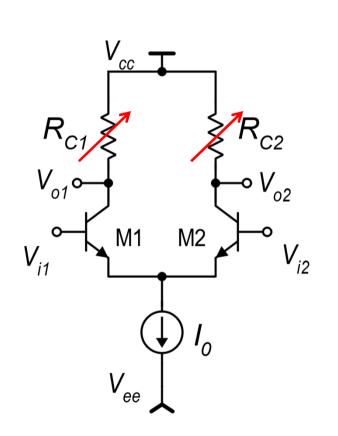
$$v_{io} = \frac{kT}{q} \left(-\frac{\Delta R_C}{R_C} - \frac{\Delta I_S}{I_S} \right)$$

$$\frac{dv_{io}}{dT} = \frac{k}{q} \left(-\frac{\Delta R_C}{R_C} - \frac{\Delta I_S}{I_S} \right)$$

These terms are practically temperature independent (ratios of homogeneous quantities)

$$\frac{dv_{io}}{dT} = \frac{kT}{q} \left(-\frac{\Delta R_C}{R_C} - \frac{\Delta I_S}{I_S} \right) \frac{1}{T} = \frac{v_{io}}{T}$$

A method to reduce the offset voltage and its drift



$$\frac{dv_{io}}{dT} = \frac{v_{io}}{T}$$

Example: v_{io} =1 mV T=300 K

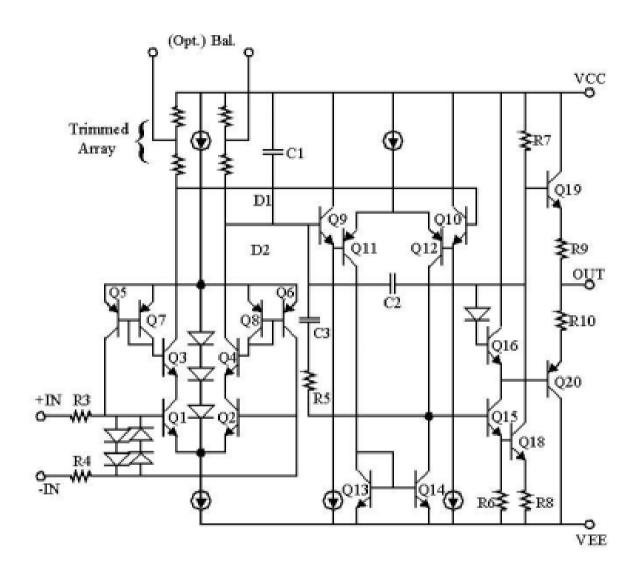
$$\frac{dv_{io}}{dT} = \frac{1.0 \times 10^{-3}}{300} = 3.3 \ \mu\text{V/K}$$

By trimming the resistors, I can null the offset. In this way, also the temperature drift is nulled.

This is an advantage of the BJT amplifier. Trimming the offset of a MOSFET differential amplifier does not null the drift.

Example: the OP07

- Resistors are varied by laser trimming to null the offset
- 2. In this way, also the offset drift is strongly reduced
- 3. The base currents of the input devices (Q1,Q2) are reproduced by Q3 and Q4 and than fed back to the input terminals by mirrors Q8,Q6 and Q7,Q5. This approach allows to reduce the input bias currents.



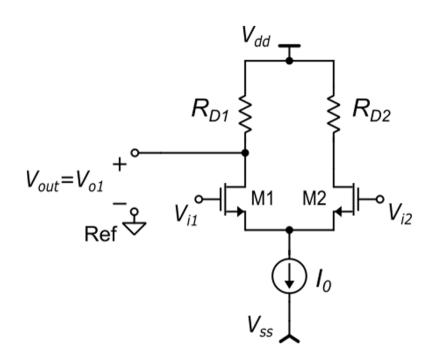
OP07 vs μA741

	Table 1.						
	Parameter	Symbol	Conditions	Min	Тур	Max	Unit
	INPUT CHARACTERISTICS						
	T _A = 25°C						
	Input Offset Voltage ¹	Vos			30	75	μV
07	Long-Term Vos Stability ²	V _{os} /Time			0.3	1.5	μV/Month
OP	Input Offset Current	los			0.5	3.8	nA
	Input Bias Current	I _B			±1.2	±4.0	nA
	0°C ≤ T _A ≤ 70°C						
	Input Offset Voltage ¹	Vos			45	130	μV
	Voltage Drift Without External Trim⁴	TCVos			0.3	1.3	μV/°C
	Voltage Drift with External Trim ³	TCV _{OSN}	$R_P = 20 \text{ k}\Omega$		0.3	1.3	μV/°C

at specified virtual junction temperature, v_{CC±} - ±10 v (unless otherwise noted)

	PARAMETER	TEST CONDITIONS ⁽¹⁾		MIN	TYP	MAX	UNIT
V	Input offset voltage	V _O = 0	25°C		1	6	mV
V _{IO}			Full range			7.5	
$\Delta V_{\text{IO(adj)}}$	Offset voltage adjust range	V _O = 0	25°C		±15		mV
	Input offset current	V ₀ = 0	25°C		20	200	nA
IIO			Full range			300	
	Input bias current	V ₀ = 0	25°C		80	500	nΛ
IB			Full range			800	nA

How is the amplifier offset when the single ended option is chosen?



$$V_{out} = V_{O1} = V_{dd} - R_1 I_{D1}$$

Single ended (S/E): device parameters do not appear as differences: the output voltage is affected mainly by global errors

The single ended case is subjected to a much larger offset!

Compare with the fully-differential case: the output voltage depends only on matching differences

$$V_{od} = R_{D2}I_{D2} - R_{D1}I_{D1}$$